

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in this application:

LISTING OF CLAIMS:

Claims 1-8. (Canceled).

9. (Currently Amended) A method for producing at least one of (a) etched holes and (b) etched trenches of a component based on one of (c) silicon and (d) a layered silicon/insulator structure, the method comprising:

applying at least one of a germanium-containing layer and a germanium layer to a back of a silicon wafer at a point at which or in whose surroundings an etching procedure is to be completed;

detecting at least one of germanium and germanium compounds during the etching procedure;

controlling the etching procedure as a function of the detection; and

completely removing at least one of the germanium and germanium-containing layer after completion of an etching procedure up to at least one of the germanium and germanium-containing layer while simultaneously separating the wafer into individual components.

10. (Previously Presented) The method according to claim 9, wherein the controlling includes interrupting the etching procedure.

11. (Previously Presented) The method according to claim 9, wherein at least one of the germanium and germanium-containing layer is buried in a layered structure.

Claims 12-14. (Canceled).

15. (Previously Presented) The method according to claim 9, wherein the at least one of germanium and germanium compounds is detected using one of optical emission spectroscopy and mass spectroscopy.

16. (Currently Amended) A diaphragm sensor unit comprising:
a substrate made of one of silicon and a layered silicon/insulator structure;
and
a flat diaphragm for implementing a sensor element structure for a sensor,
wherein at least one of a germanium and germanium-containing layer ~~is simultaneously used as a component functional layer and~~ is situated in the layered structure,
wherein the at least one of the germanium and germanium-containing layer is completely removed after completion of an etching procedure up to at least one of the germanium and germanium-containing layer while simultaneously separating the wafer into individual components.

17. (Previously Presented) The diaphragm sensor unit according to claim 16, wherein the flat diaphragm contains germanium.

18. (Previously Presented) The diaphragm sensor unit according to claim 16, wherein the flat diaphragm is made entirely of germanium.